

## INFORMATION DISCLOSURE STATEMENT

(Use Several Sheets if necessary)

ATTY DOCKET NO.

UTC 005

APPLICATION NO.

90/896,955

APPLICANT

George et al.

FILING DATE

June 29, 2001

GROUP

2811

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE

## FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION YES   NO
					<input type="checkbox"/>   <input type="checkbox"/>

## OTHER DISCLOSURES (Including Author, Title, Date, Pertinent Pages, Place of Publication, Etc.)

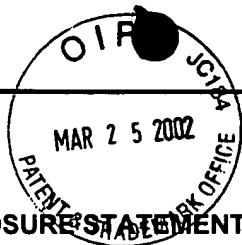
Thm	Deal et al., ELECTRICAL PROPERTIES OF VAPOR-DEPOSITED SILICON NITRATE..., March 1968, J. Electrochem. Soc., pgs. 300-307
	Van Cauwelaert et al., INFRA-RED SPECTROSCOPIC STUDY OF THE ABSORPTION OF..., June 1971, Laboratorium voor Oppervlakteskunde, pgs. 66-76
	Goto et al., DIELECTRIC PROPERTIES OF CHEMICALLY VAPOR-DEPOSITED Si <sub>3</sub> N <sub>4</sub> , 1989, Journal of Materials Science 24, pgs. 821-826
	Blitz et al., THE ROLE OF AMINE STRUCTURE ON CATALYTIC ACTIVITY..., 1988, Journal of Colloid and Interface Science-Vol. 26-No. 2, pgs. 387-392
	Blitz et al., AMMONIA-CATALYZED SILYLATION REACTIONS OF CAB-O-SIL WITH METHOXYMETHYLSILANES, 1987, J. Am. Chem. Soc., pgs. 7141-7145
	Adams et al., THE DEPOSITION OF SILICON DIOXIDE FILMS AT REDUCED PRESSURE, June 1979, J. Electrochem. Soc. pgs. 1042-1046
	Wanatabe et al., THE PROPERTIES OF LPCVD SiO <sub>2</sub> FILM..., December 1981, J. Electrochem. Soc. Pgs. 2630-2635
	Becker et al., LOW PRESSURE DEPOSITION OF HIGH-QUALITY SiO <sub>2</sub> FILMS..., 1987, J. Vac. Sci. Technol. B 5 (6), pgs. 1555-1563
	Kern et al., ADVANCES IN DEPOSITION PROCESSES FOR PASSIVATION FILMS, 1977, J. Vac. Sci. Technol.-Vol. 14-No. 5, Pgs. 1082-1099
	Morishita et al., ATOMIC-LAYER CHEMICAL-VAPOR-DEPOSITION OF SiO <sub>2</sub> ..., 1995, Jpn. J. Appl. Phys. Vol. 34, pgs. 5738-5742
Thm	Morishita et al., NEW SUBSTANCES FOR ATOMIC-LAYER DEPOSITION OF SILICON DIOXIDE, 1995, Journal of Non-Crystalline Solids 187, pgs. 66-69

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					<input type="checkbox"/>   <input type="checkbox"/>

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Thm	✓	Tripp et al., CHEMICAL ATTACHMENT OF CHOROSILANES TO SILICA..., 1993, J. phys. Chem. 97, pgs. 5693-5698
	✓	Ehrlich et al., FAST ROOM TEMPERATURE GROWTH OF SiO <sub>2</sub> FILMS..., 1991, Appl. Phys. Lett. 58 (23), pgs. 2675-5677
		Klaus et al., ATOMIC LAYER CONTROLLED GROWTH OF Si <sub>3</sub> N <sub>4</sub> ..., 1998, Surface Science, pgs. L14-L19
	✓	Klaus et al., ATOMIC LAYER DEPOSITION OF SiO <sub>2</sub> ..., 2000, Surface Science 447, pgs. 81-90
	✓	Klaus et al., ATOMIC LAYER DEPOSITION OF SiO <sub>2</sub> ..., 1999, Surface Review and Letters-Vol. 6-Nos. 3 and 4, pgs. 435-448
Thm	✓	Klaus et al., GROWTH OF SiO <sub>2</sub> AT ROOM TEMPERATURE..., December 1997, Science-Vol. 278, pgs. 1934-1936

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